

Supplementary Information

Triethanolamine Doped Multilayer MoS₂

Field Effect Transistors

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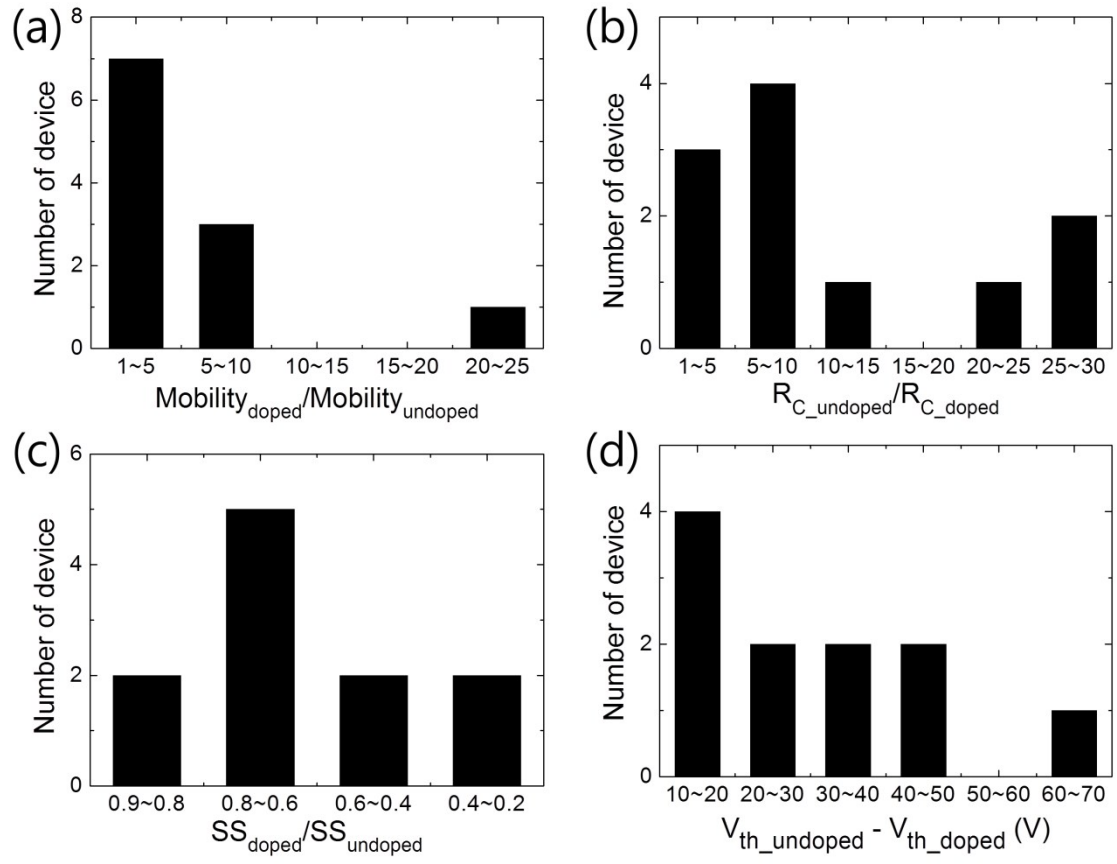


Figure S1 Distribution of mobility ratio (a), contact resistance (R_{C}) ratio (b), subthreshold swing (SS) ratio (c) and threshold voltage (V_{th}) shift (d) before and after the doping process.

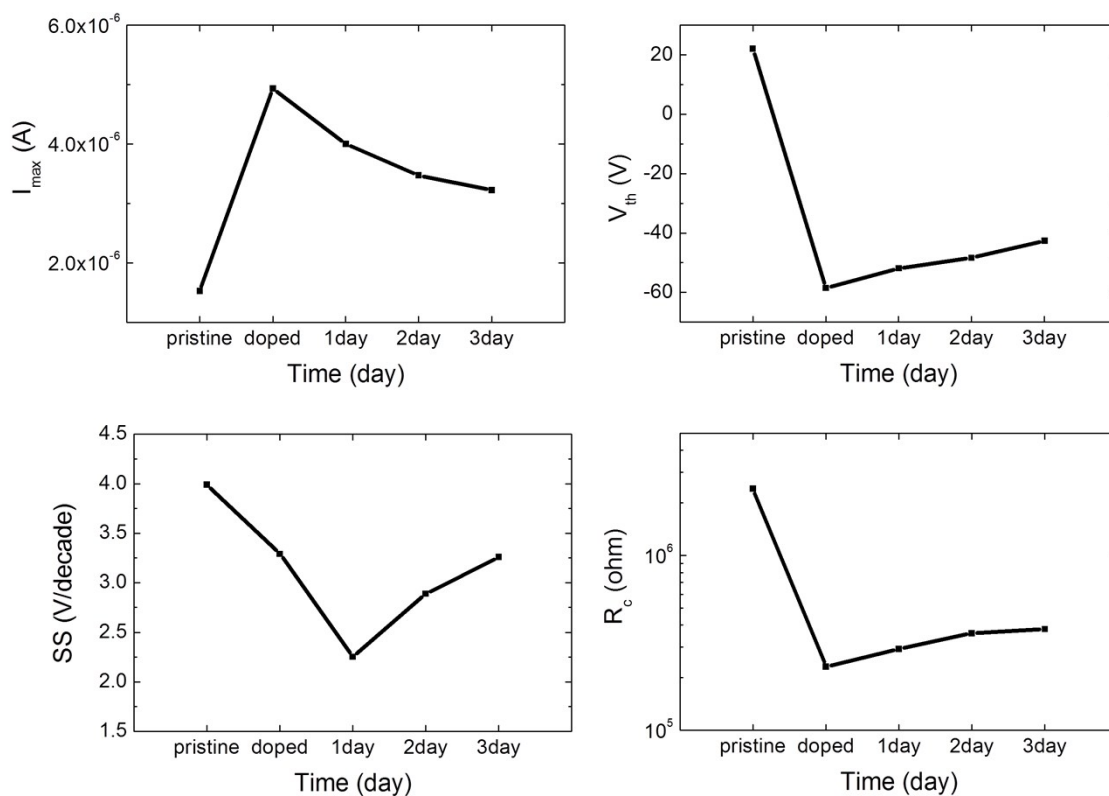


Figure. S2 Stability of on-current (a), threshold voltage (V_{th}) (b), subthreshold swing (SS) (c) and contact resistance (R_c) (d) in air for 3 days before and after the doping process.

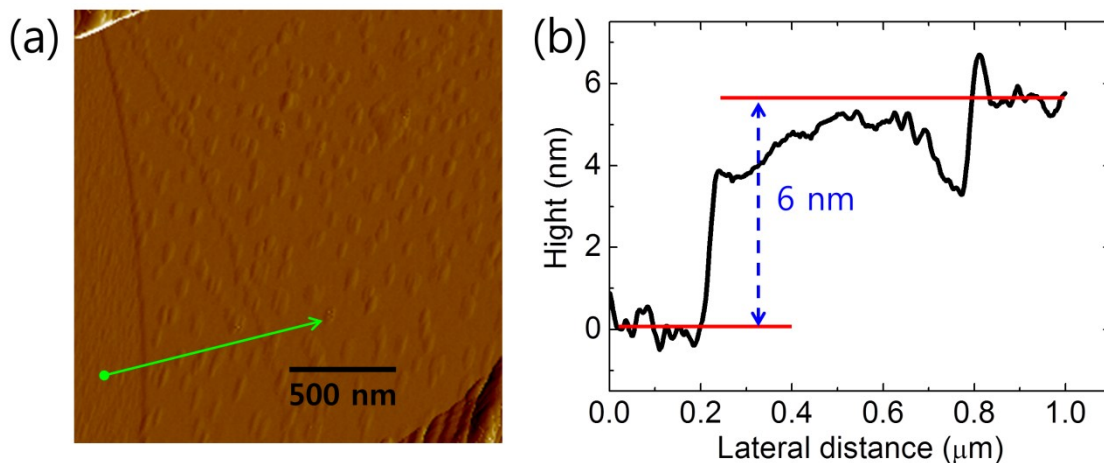


Figure. S3 (a) AFM image of multilayer MoS_2 . (b) Height profile measured along the green line in figure S3(a).